

isc N-Channel MOSFET Transistor

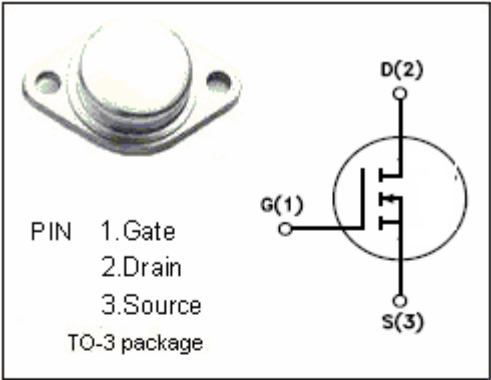
2N6755

DESCRIPTION

- VGS Rated at ±20V
- Silicon Gate for fast switching speeds
- IDSS 、 RDS(ON) ,specified at elevated temperature
- Low drive requirements

APPLICATIONS

designed for high power ,high speed application ,such as switching applies,UPS,AC and DC motor controls , relay and high energy pulse circuits.

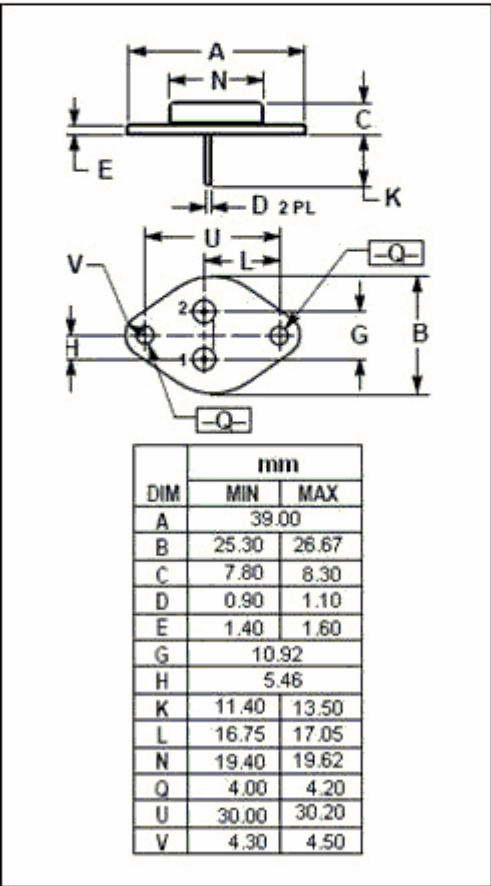


ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	ARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-continuous@ TC=37°C	12	A
P _{tot}	Total Dissipation@TC=25°C	75	W
T _j	Max. Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature Range	-55~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	1.67	°C/W



isc N-Channel Mosfet Transistor**2N6755****• ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0$; $I_D=1\text{mA}$	60		V
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$; $I_D=1\text{mA}$	2	4	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	$V_{GS}=10\text{V}$; $I_D=8\text{A}$		0.25	Ω
I_{GSS}	Gate Source Leakage Current	$V_{GS}=20\text{V}$; $V_{DS}=0$		100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60\text{V}$; $V_{GS}=0$		1	mA
V_{SD}	Diode Forward Voltage	$I_F=12\text{A}$; $V_{GS}=0$		1.7	V